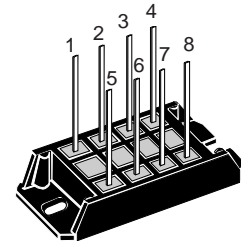
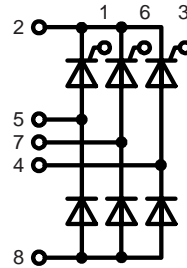


## Three Phase Half Controlled Rectifier Bridge

$I_{dAVM} = 43 \text{ A}$   
 $V_{RRM} = 1200-1600 \text{ V}$

$V_{RSM}$ $V_{DSM}$ V	$V_{RRM}$ $V_{DRM}$ V	Type
1300	1200	VVZ 40-12io1
1500	1400	VVZ 40-14io1
1700	1600	VVZ 40-16io1



Symbol	Test Conditions	Maximum Ratings	Features	
$I_{dAV}$ $I_{dAVM}$ $I_{FRMS}^2, I_{TRMS}$	$T_K = 100^\circ\text{C}$ ; module module per leg	34 A 43 A 25 A	<ul style="list-style-type: none"> <li>• Package with DCB ceramic base plate</li> <li>• Isolation voltage 3600 V~</li> <li>• Planar passivated chips</li> <li>• Soldering terminals</li> <li>• UL registered E 72873</li> </ul>	
$I_{FSM}^2, I_{TSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine		320 A 340 A
	$T_{VJ} = T_{VJM}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine		290 A 310 A
$I^2t$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine		510 A <sup>2</sup> s 485 A <sup>2</sup> s
	$T_{VJ} = T_{VJM}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine		420 A <sup>2</sup> s 400 A <sup>2</sup> s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $f = 400 \text{ Hz}$ , $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$ , $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	repetitive, $I_T = 50 \text{ A}$ non repetitive, $I_T = 1/3 \cdot I_{dAV}$		150 A/ $\mu\text{s}$ 500 A/ $\mu\text{s}$
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$ ; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$ ; method 1 (linear voltage rise)			1000 V/ $\mu\text{s}$
$V_{RGM}$				10 V
$P_{GM}$	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30 \mu\text{s}$ $t_p = 500 \mu\text{s}$ $t_p = 10 \text{ ms}$		$\leq 10 \text{ W}$ $\leq 5 \text{ W}$ $\leq 1 \text{ W}$
$P_{GAVM}$				0.5 W
$T_{VJ}$ $T_{VJM}$ $T_{stg}$			-40...+125 °C 125 °C -40...+125 °C	
$V_{ISOL}$	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ min}$ $t = 1 \text{ s}$	3000 V~ 3600 V~	
$M_d$	Mounting torque	(M5) (10-32 UNF)	2-2.5 Nm 18-22 lb.in.	
Weight	typ.		28 g	

### Features

- Package with DCB ceramic base plate
- Isolation voltage 3600 V~
- Planar passivated chips
- Soldering terminals
- UL registered E 72873

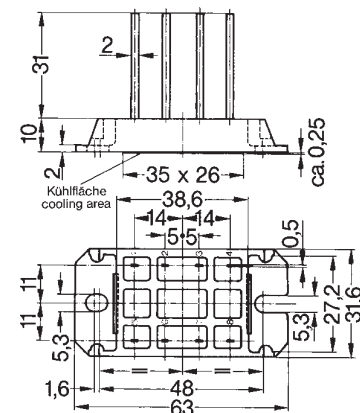
### Applications

- Input rectifier for switch mode power supplies (SMPS)
- Softstart capacitor charging
- Electric drives and auxiliaries

### Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

### Dimensions in mm (1 mm = 0.0394")



Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.  
 IXYS reserves the right to change limits, test conditions and dimensions.

Symbol	Test Conditions	Characteristic Values
$I_R, I_D$	$V_R = V_{RRM}; V_D = V_{DRM}$ $T_{VJ} = T_{VJM}$ $T_{VJ} = 25^\circ\text{C}$	$\leq 5$ mA $\leq 0.3$ mA
$V_F, V_T$	$I_F, I_T = 30$ A, $T_{VJ} = 25^\circ\text{C}$	$\leq 1.33$ V
$V_{TO}$	For power-loss calculations only	0.85 V
$r_T$	( $T_{VJ} = 125^\circ\text{C}$ )	15 m $\Omega$
$V_{GT}$	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	$\leq 1.0$ V $\leq 1.2$ V
$I_{GT}$	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	$\leq 65$ mA $\leq 80$ mA $\leq 50$ mA
$V_{GD}$	$T_{VJ} = T_{VJM};$ $T_{VJ} = T_{VJM};$	$\leq 0.2$ V $\leq 5$ mA
$I_{GD}$	$V_D = 2/3 V_{DRM}$ $V_D = 2/3 V_{DRM}$	
$I_L$	$I_G = 0.3$ A; $t_G = 30$ $\mu\text{s}$ $di_G/dt = 0.3$ A/ $\mu\text{s}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	$\leq 150$ mA $\leq 200$ mA $\leq 100$ mA
$I_H$	$T_{VJ} = 25^\circ\text{C}; V_D = 6$ V; $R_{GK} = \infty$	$\leq 100$ mA
$t_{gd}$	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.3$ A; $di_G/dt = 0.3$ A/ $\mu\text{s}$	$\leq 2$ $\mu\text{s}$
$t_q$	$T_{VJ} = 125^\circ\text{C}; I_T = 15$ A, $t_p = 300$ $\mu\text{s}$ , $-di/dt = 10$ A/ $\mu\text{s}$	typ. 150 $\mu\text{s}$
$Q_r$	$V_R = 100$ V, $dv/dt = 20$ V/ $\mu\text{s}$ , $V_D = 2/3 V_{DRM}$	75 $\mu\text{C}$
$R_{thJC}$	per thyristor (diode); DC current	1.0 K/W
	per module	0.17 K/W
$R_{thJH}$	per thyristor (diode); DC current	1.6 K/W
	per module	0.27 K/W
$d_s$	Creeping distance on surface	7 mm
$d_A$	Creepage distance in air	7 mm
$a$	Max. allowable acceleration	50 m/s <sup>2</sup>